

Fig.1(A)

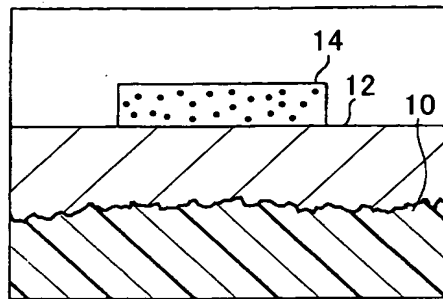


Fig.1(B)

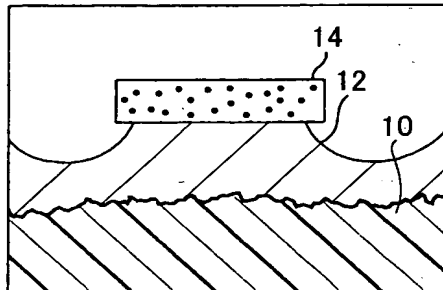


Fig.1(C)

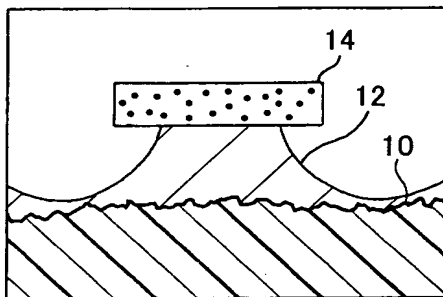


Fig.1(D)

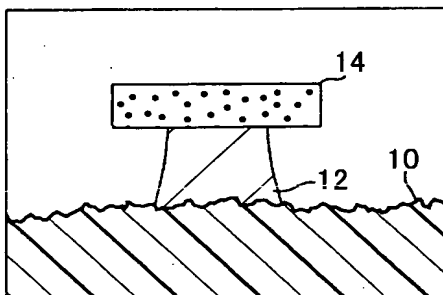


Fig.1(E)

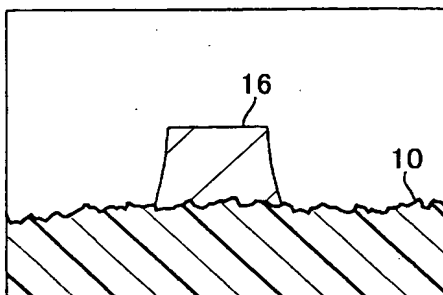


Fig.2(A)

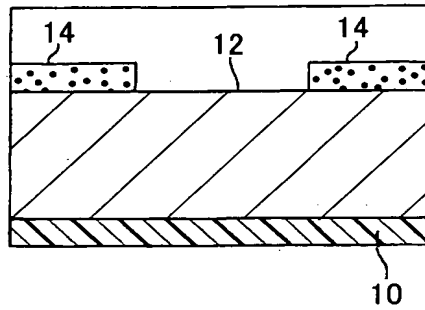


Fig.2(B)

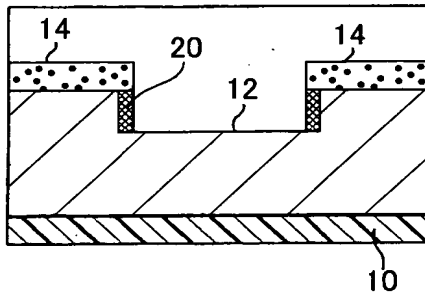


Fig.2(C)

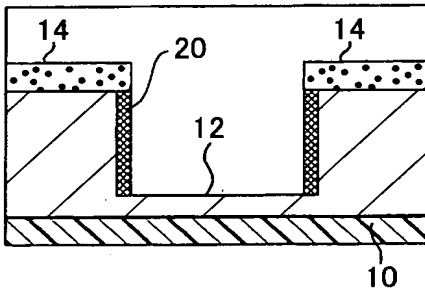


Fig.2(D)

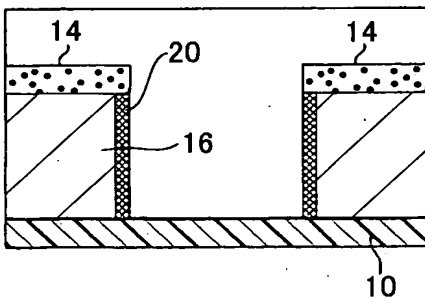


Fig.3(A)

Etching reaction process
 (Prior art)

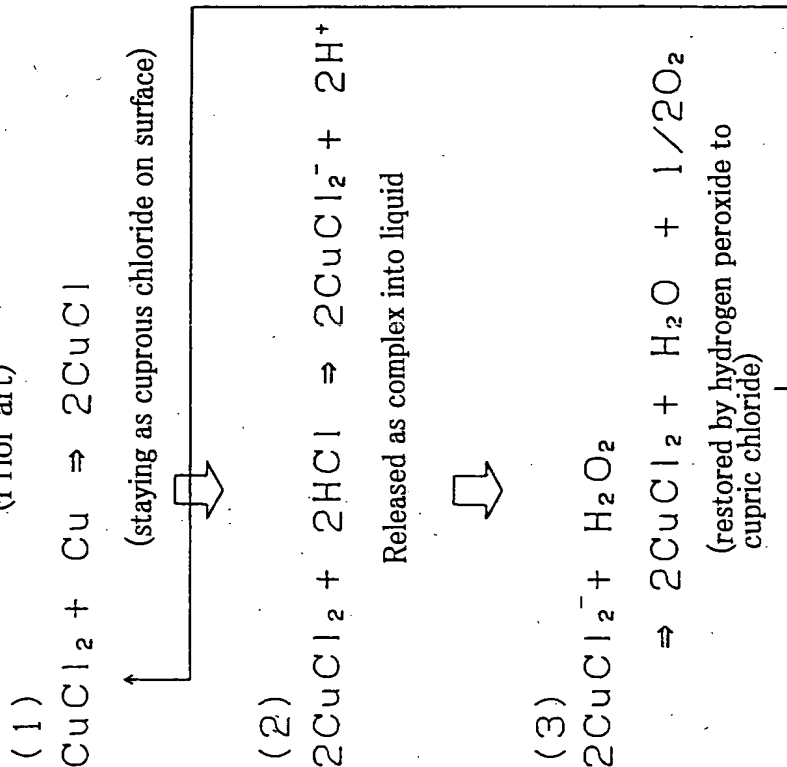


Fig.3(B)

Etching reaction process
 (Present invention)

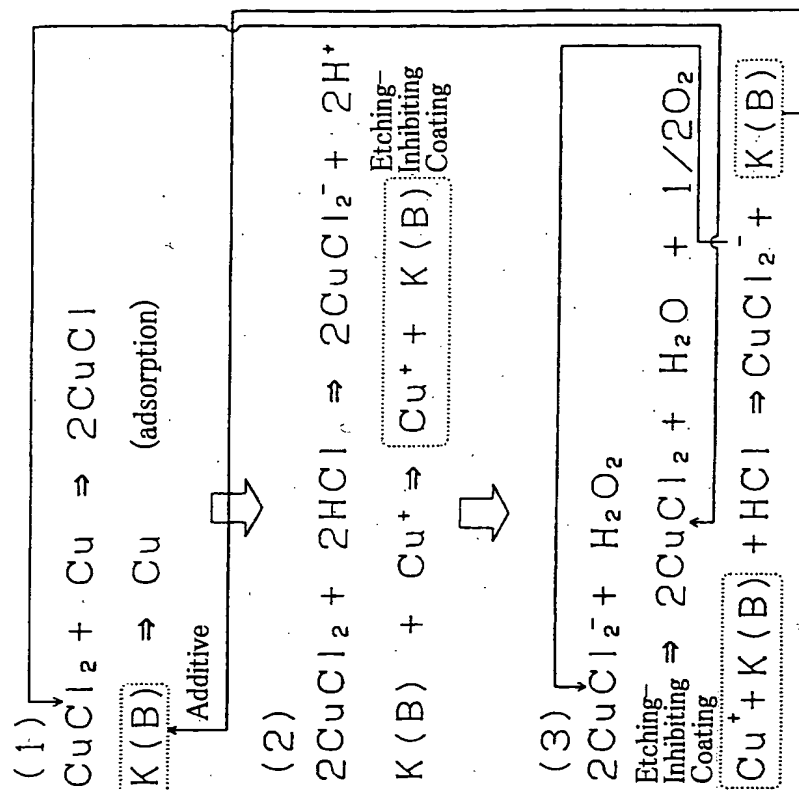


Fig.4(A) STRUCTURE

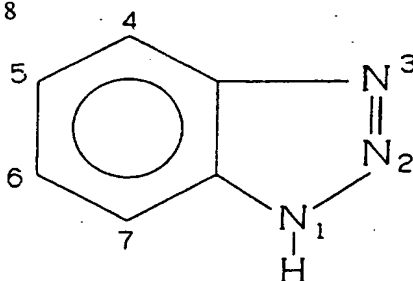


Fig.4(B) BTA

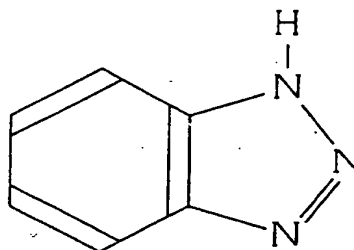


Fig.4(C) TTA

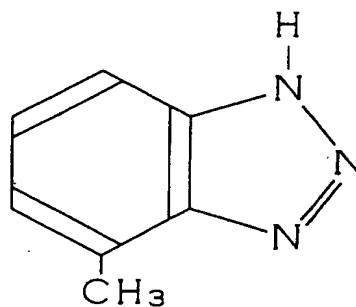


Fig.4(D) BTA-COOH

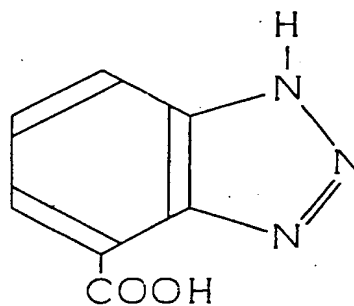


Fig. 5(A1)

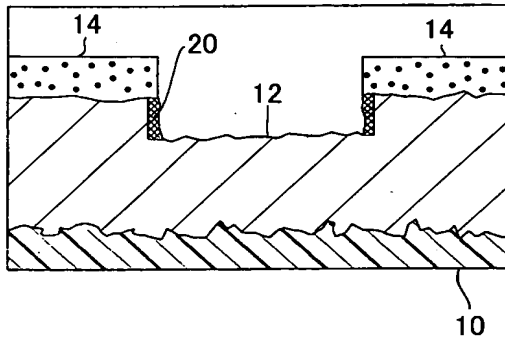


Fig. 5(B1)

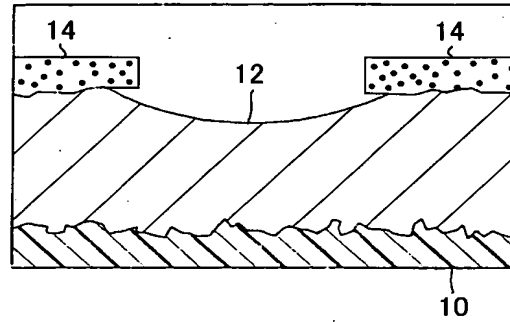


Fig. 5(A2)

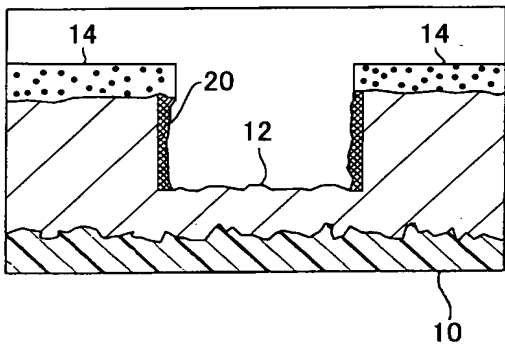


Fig. 5(B2)

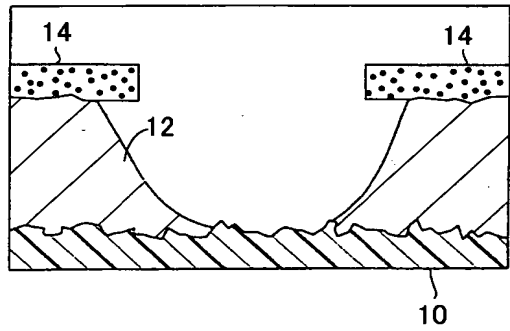


Fig. 5(A3)

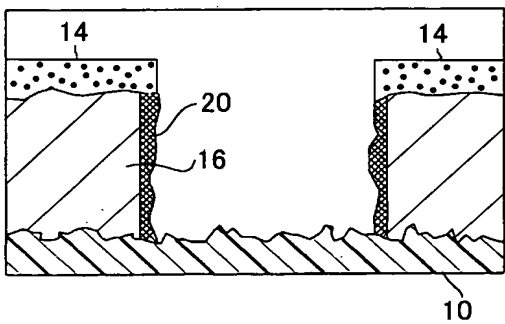


Fig. 5(B3)

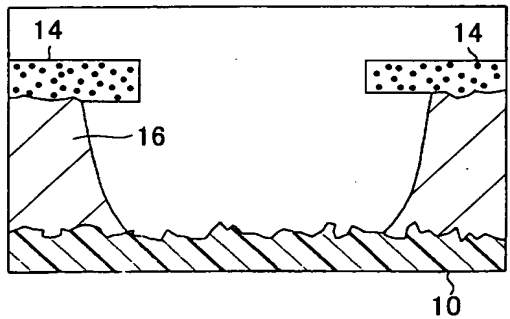


Fig. 6
 Configuration of wiring pattern
 (Prior art)

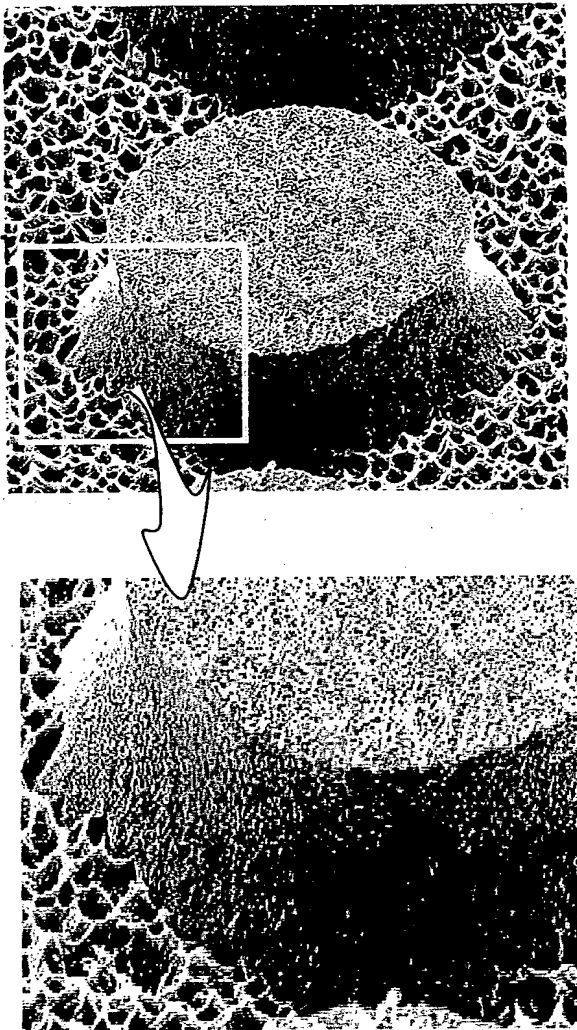


Fig. 7
 Configuration of wiring pattern
 (Present invention)

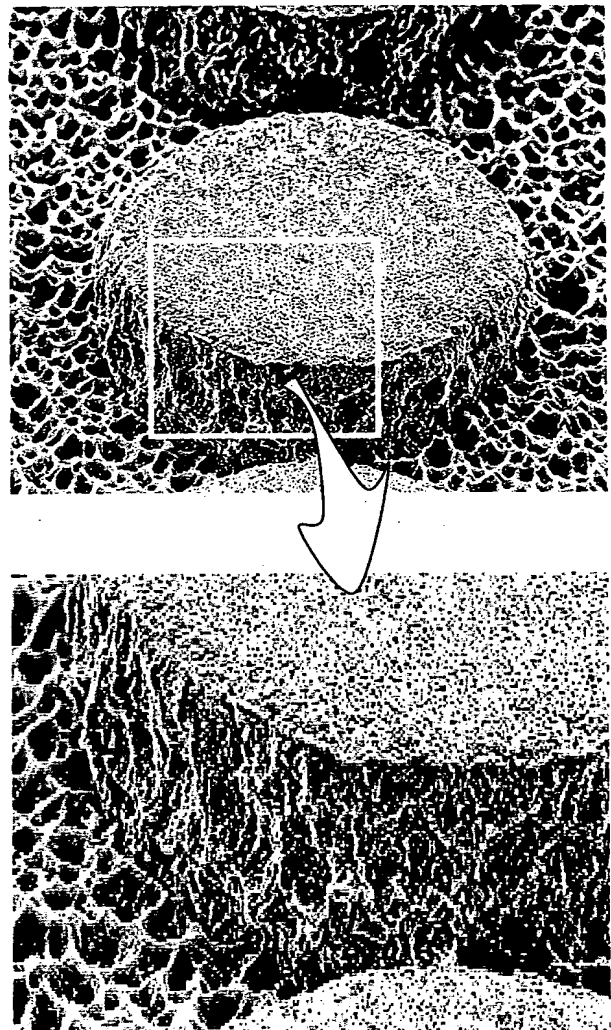


Fig. 8

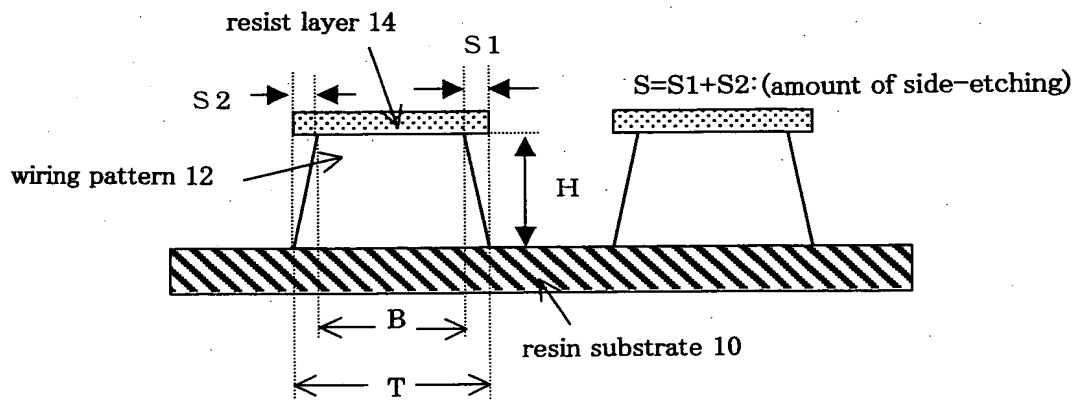
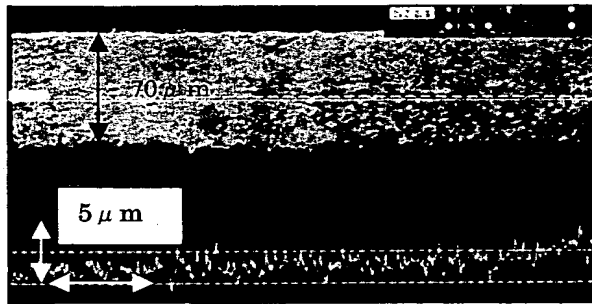


Fig. 9(A) (After etching)

Fig. 10(A) (After etching)

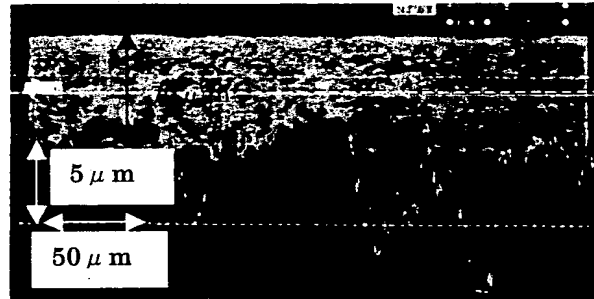
Prior art

Present invention



50 μ m

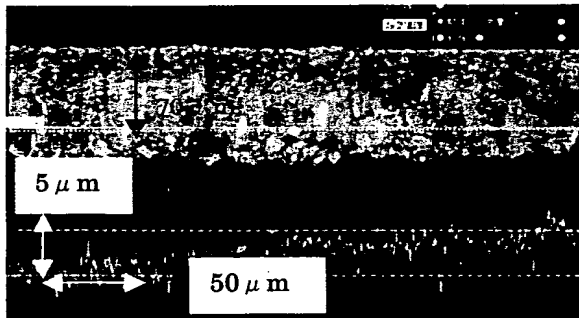
Rmax:2.25 μ m



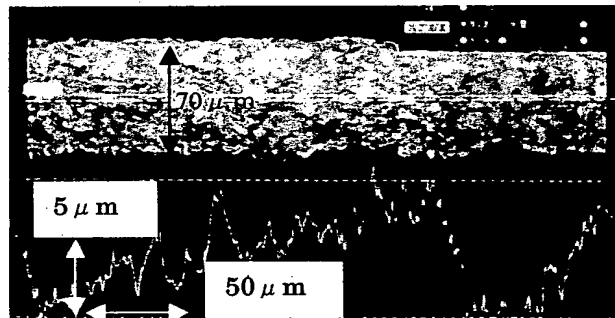
Rmax:9.47 μ m

Fig. 9(B) (After CZ roughing processing)

Fig.10(B) (After CZ roughing processing)



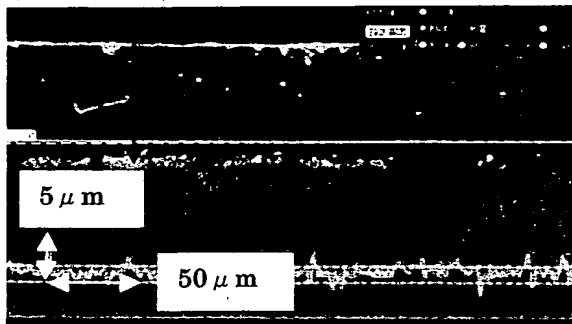
Rmax:2.81 μ m



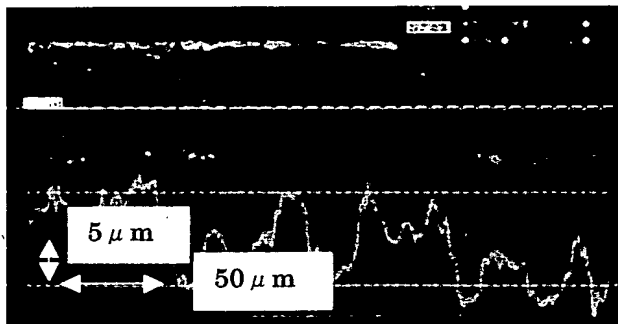
Rmax:11.17 μ m

Fig. 9(C) (After blackening process)

Fig.10(C) (After blackening process)



Rmax:1.63 μ m



Rmax:10.87 μ m

Fig. 11

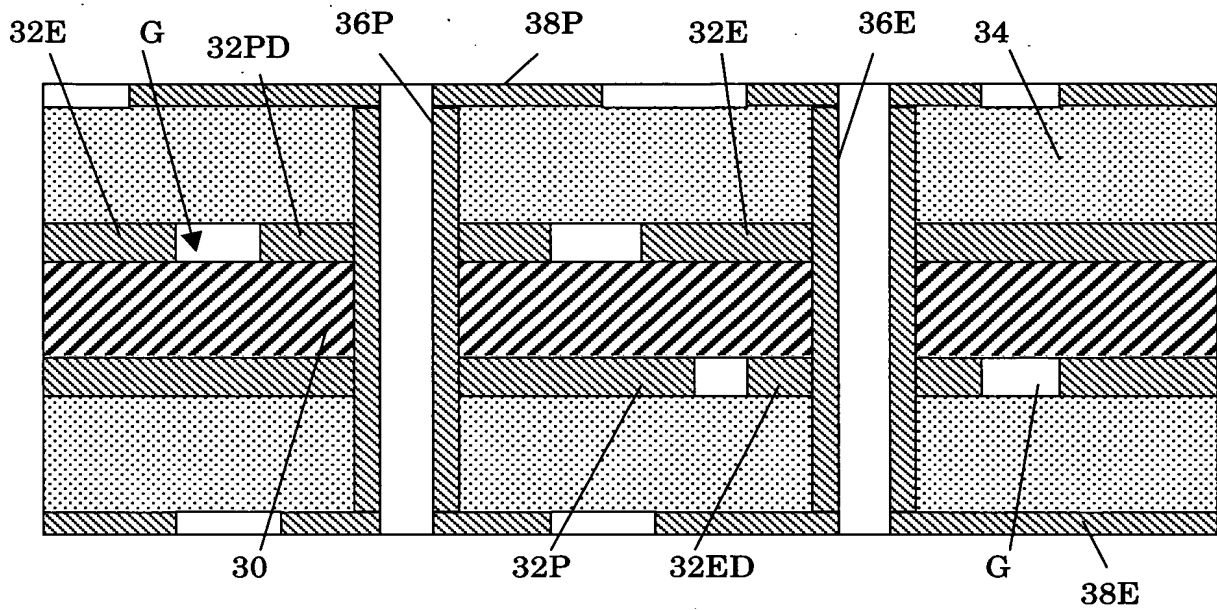


Fig. 12(A)

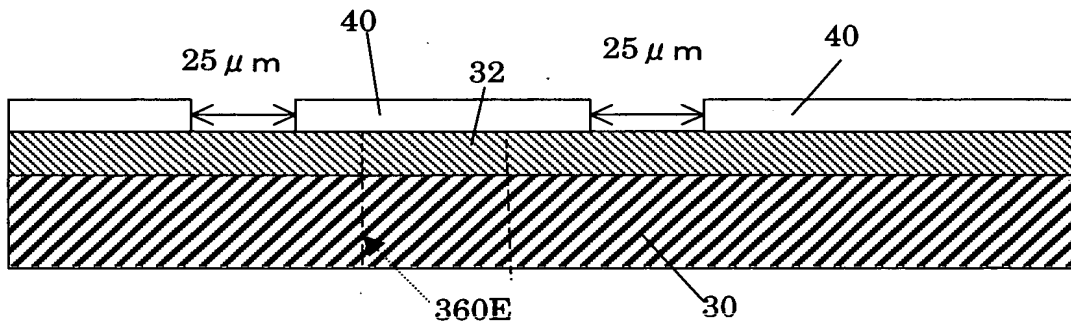


Fig. 12(B)

